• 1N5711-1 AVAILABLE IN JAN, JANTX, JANTXV AND JANS PER MIL-PRF-19500/444

• 1N5712-1 AVAILABLE IN JAN, JANTXV AND JANS PER MIL-PRF-19500/445

SCHOTTKY BARRIER DIODES

• HERMETICALLY SEALED

• METALLURGICALLY BONDED

1N5711 1N5711-1 1N5712-1 1N6857-1 1N6858-1 DSB2810 DSB5712

MAXIMUM RATINGS

Operating Temperature: -65° C to $+150^{\circ}$ C Storage Temperature: -65° C to $+150^{\circ}$ C

Operating Current: 5711 types :33mA dc@ $T_L = +130$ °C, L = 3/8"

Derating: 1.75 IIA GC = 1.75 IIA GC =

ELECTRICAL CHARACTERISTICS @ 25°C, unless otherwise specified.

							m (2)
CDI	MINIMUM	MAXIMUM	MAXIMUM	MAXIMUM REVERSE LEAKAGE CURRENT		MAXIMUM	ESDS
TYPE	BREAKDOWN	FORWARD	FORWARD			CAPACITANCE @	CLASS
NUMBER	VOLTAGE	VOLTAGE	VOLTAGE	I _R @ V _R		V R = 0 VOLTS	10
						f = 1.0 MHz	-
	${ m V_{BR}}$ @ 10 $_{\mu}$ A	V _F @ 1 mA	ν _F @ ι _F				C _T
	VOLTS	VOLTS	MILLIAMPS	nA	VOLTS	PICO FARADS	
DSB2810	20	0.41	1.0@35	100	15	2.0	1
1N5711,-1	70	0.41	1.0@15	200	50	2.0	1
DSB5712	20	0.41	1.0@35	150	16	2.0	1
1N5712-1	20	0.41	1.0@35	150	16	2.0	1
1N6857-1	20	0.35	0.75@35	150	16	4.5	2
1N6858-1	70	0.36	0.65@15	200	50	4.5	2

NOTE: Effective Minority Carrier Lifetime (τ) is 100 Pico Seconds

NOTICE: Qualification testing to M, JX, and JS levels for 6857 and 6858 types is underway.

Contact the factory for qualification completion dates. These two part numbers are being introduced by CDI as "drop-in" replacements for the 5711 and 5712. They provide a more robust mechanical design and a higher ESDS class with the only

trade-off being an increase in capacitance.

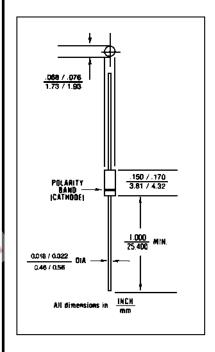


FIGURE 1

DESIGN DATA

CASE: Hermetically sealed glass case per MIL-PRF-19500/444 and /445 DO-35 Outline

LEAD MATERIAL: Copper clad steel.

LEAD FINISH: Tin / Lead

THERMAL RESISTANCE: (R_QJEC): 250

°C/W maximum at L = .375 inch

THERMAL IMPEDANCE: (ZQJX): 40

°C/W maximum

POLARITY: Cathode end is banded.

MOUNTING POSITION: Any.



COMPENSATED DEUICES INCORPORATED

1N5711, 1N5712, 1N6857, 1N6858 DSB5712 and DSB2810 INCLUDING -1 VERSIONS

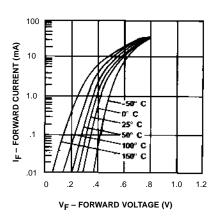
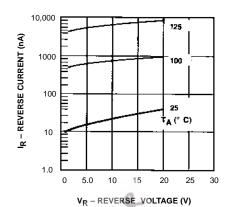


Figure 1.
I-V Curve Showing Typical
Forward Voltage Variation with
Temperature for the DSB5712 and
DSB2810 Schottky Diodes.



(PULSED)
Figure 2.
DSB5712 and DSB2810
Typical Variation of Reverse
Current (I_R) vs. Reverse Voltage
(V_R) at Various Temperatures.

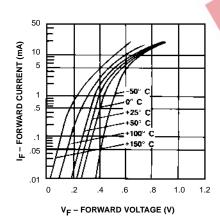


Figure 3.
I-V Curve Showing Typical
Forward Voltage Variation with
Temperature for Schottky Diode

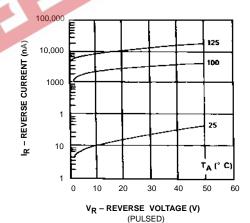
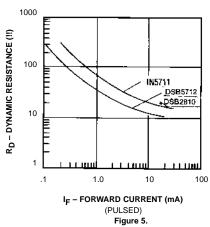


Figure 4.

1N5711 Typical

Variation of Reverse Current (I_R)
vs. Reverse Voltage (V_R) at
Various Temperatures.



(PULSED)
Figure 5.
Typical Dynamic
Resistance (R_D) vs. Forward
Current (I_F).